TOSHIBA ALLOY-FREE HIGHT SPEED THYRISTOR

S H 4 O O R 2 9 B

HIGH POWER CONTROL APPLICATIONS

Repetitive Peak Off-State Voltage: VDRM) =1300V

Repetitive Peak Reverse Voltage : VRRM

Average On-State Current $: I_{T(AV)} = 400A$

Turn-Off Time : $t_0 = 25 \mu s$ (Max.)

Critical Rate of Rise of On-State Current

: $di/dt = 200A/\mu s$

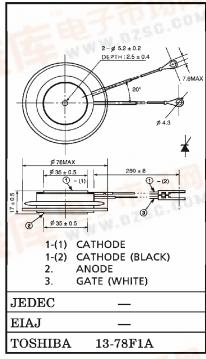
Critical Rate of Rise of Off-State Voltage

: $dv/dt = 500V/\mu s$

Weight : 260g

Flat Package

Unit in mm



The information contained herein is subject to change without notice.

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MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	$rac{ m V_{DRM}}{ m V_{RRM}}$	1300	v
Non-Repetitive Peak Reverse Voltage (Non-Repetitive $< 5 \text{ms}, T_j = 0 \sim 125^{\circ}\text{C}$)	$v_{ m RSM}$	1400	V
R.M.S On-State Current	IT (RMS)	628	A
Average On-State Current	I _T (AV)	400	Α
Peak One Cycle Surge On-State Current (Non-Repetitive)	ITSM	7200 (50Hz) 8000 (60Hz)	V
I ² t Limit Value	${f I}^2{f t}$	200×10^{3}	$ m A^2s$
Critical Rate of Rise of On-State Current (Note)	di/dt	200	A/μs
Peak Gate Power Dissipation	P_{GM}	20	W
Average Gate Power Dissipation	P _G (AV)	4	W
Peak Forward Gate Current	I_{GM}	4	A
Peak Forward Gate Voltage	v_{FGM}	20	V
Peak Reverse Gate Voltage	v_{RGM}	5	V
Junction Temperature	T_{j}	-40~115	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~115	$^{\circ}\mathrm{C}$
Mounting Force	_	14.7 ± 1.5	kN

Note : V_D=1/2 Rated, T_j=110°C, Gate Supply (V_G=15V, R_G=8\Omega, t_r $\!\leq\! 1\mu s$)

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	MAX.	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	IDRM IRRM	$V_{ m DRM} = V_{ m RRM} = { m Rated}$ $T_{ m j} = 115 { m ^{\circ}C}$		_	50	mA
Peak On-State Voltage	$ m V_{TM}$	$I_{TM} = 1250A, T_j = 25^{\circ}C$			2.2	V
Gate Trigger Voltage	v_{GT}	W 0V D 00	$T_j = -40^{\circ}C$ $T_j = 25^{\circ}C$	_	4.5 3.5	V
Gate Trigger Current	I_{GT}	l —	$T_j = -40^{\circ}C$ $T_j = 25^{\circ}C$	_	400 260	mA
Gate Non-Trigger Voltage	$v_{ m GD}$	V _D =1/2 Rated, T _j =115°C		0.2	_	V
Gate Non-Trigger Current	$^{\mathrm{I}}\mathrm{GD}$			5		mA
Delay Time	$^{\mathrm{t}}\mathrm{d}$	V_D =1/2 Rated, T_j =25°C Gate Supply (V_G =15V, R_G =8 Ω , t_r \leq 1 μ s)		_	4	μs
Gate Turn-On Time	t_{gt}			_	6	μs
Turn-Off Time	t_{q}	I_{TM} =800A, V_R \geq 50V dv/dt=20V/\mu s, T_j =110°C V_{DRM} =1/2 Rated		_	25	μs
Holding Current	${ m I_{H}}$	$T_j=25$ °C, $R_L=6\Omega$			400	mA
Critical Rate of Rise of Off-State Voltage	dv / dt	V _{DRM} =1/2 Rated, T _j =115°C Gate Open, Exponential Rise		500	_	V/μs
Thermal Resistance (Junction to Case)	$ m R_{th~(j-f)}$	DC		_	0.04	°C/W

